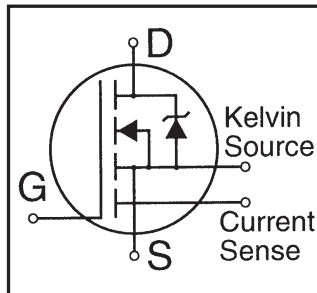


HEXFET® Power MOSFET

- Dynamic dv/dt Rating
- Current Sense
- 175°C Operating Temperature
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements

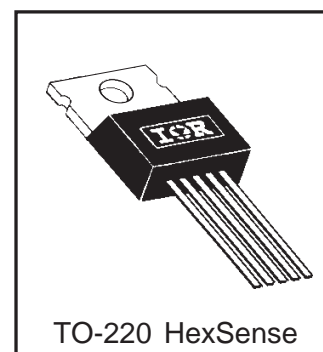


$V_{DSS} = 55V$
$R_{DS(on)} = 0.040\Omega$
$I_D = 26A$

Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device, low on-resistance and cost-effectiveness.

The HEXSense device provides an accurate fraction of the drain current through the additional two leads to be used for control or protection of the device. These devices exhibit similar electrical and thermal characteristics as their IRF-series equivalent part numbers. The provision of a kelvin source connection effectively eliminates problems of common source inductance when the HEXSense is used as a fast, high-current switch in non current-sensing applications.



Absolute Maximum Ratings

Parameter		Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	17	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	12	
I_{DM}	Pulsed Drain Current ①	68	
$P_D @ T_C = 25^\circ C$	Power Dissipation	60	W
	Linear Derating Factor	0.40	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ②	6.0	mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.5	A
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting Torque, 6-32 or screw	10 lbf•in (1.1 N•m)	

Thermal Resistance

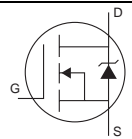
	Parameter	Min.	Max.	Units	
$R_{\theta JC}$	Junction-to-Case	—	—	2.5	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	—	62	

**When mounted on FR-4 board using minimum recommended footprint. For recommended footprint and soldering techniques refer to application note #AN-994.

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Parameter		Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	60	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.061	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1mA$
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	—	—	0.10	Ω	$V_{GS} = 10V, I_D = 10A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	5.8	—	—	S	$V_{DS} = 25V, I_D = 10A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	25		$V_{DS} = 60V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 48V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100		$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
Q_g	Total Gate Charge	—	—	24		$I_D = 17A$
Q_{gs}	Gate-to-Source Charge	—	—	6.3	nC	$V_{DS} = 48V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	9.0		$V_{GS} = 10V$, See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	12	—		$V_{DD} = 30V$
t_r	Rise Time	—	59	—		$I_D = 17A$
$t_{d(off)}$	Turn-Off Delay Time	—	25	—		$R_G = 18\Omega$
t_f	Fall Time	—	38	—		$R_D = 1.7\Omega$, See Fig. 10 ④
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6 mm (0.25 in.) from package and center of die contact
L_C	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	720	—		$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	360	—	pF	$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	75	—		$f = 1.0MHz$, See Fig. 5
r	Current Sensing Ratio	740	—	820	—	$I_D = 17A, V_{GS} = 10V$
C_{oss}	Output Capacitance of Sensing Cells	—	14	—	pF	$V_{GS} = 0V, V_{DS} = 25V, f = 1.0MHz$

Source-Drain Ratings and Characteristics

Parameter	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	17	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	68		
V_{SD}	Diode Forward Voltage	—	—	1.5	V	$T_J = 25^\circ\text{C}, I_S = 17A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	87	180	ns	$T_J = 25^\circ\text{C}, I_F = 17A$
Q_{rr}	Reverse Recovery Charge	—	0.29	0.60	nC	$di/dt = 100A/\mu s$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

③ $I_{SD} \leq 17A, di/dt \leq 140A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$

② $V_{DD} = 25V$, starting $T_J = 25^\circ\text{C}$, $L = 0.024mH$
 $R_G = 25\Omega, I_{AS} = 17A$. (See Figure 12)

④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

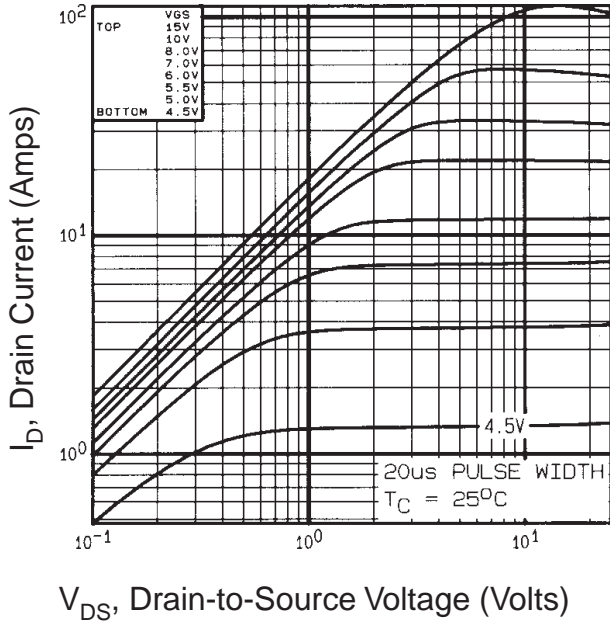


Fig. 1 Typical Output Characteristics,
 $T_C=25^\circ\text{C}$

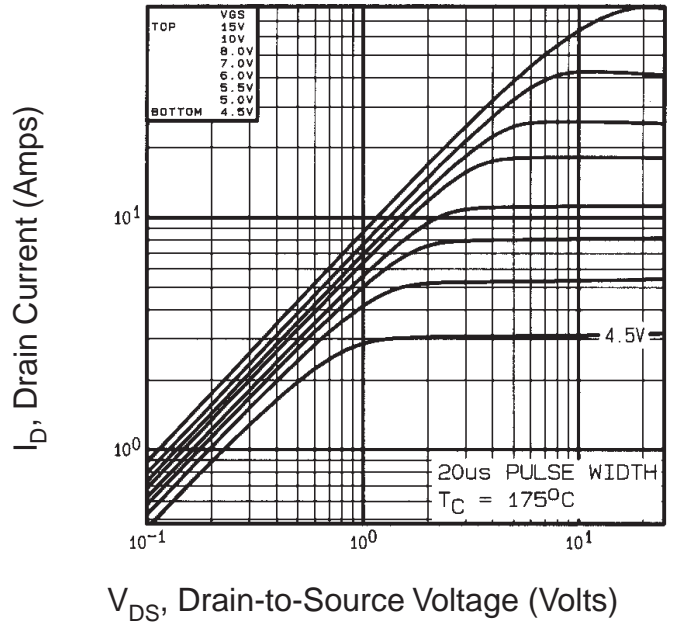


Fig. 2 Typical Output Characteristics,
 $T_C=175^\circ\text{C}$

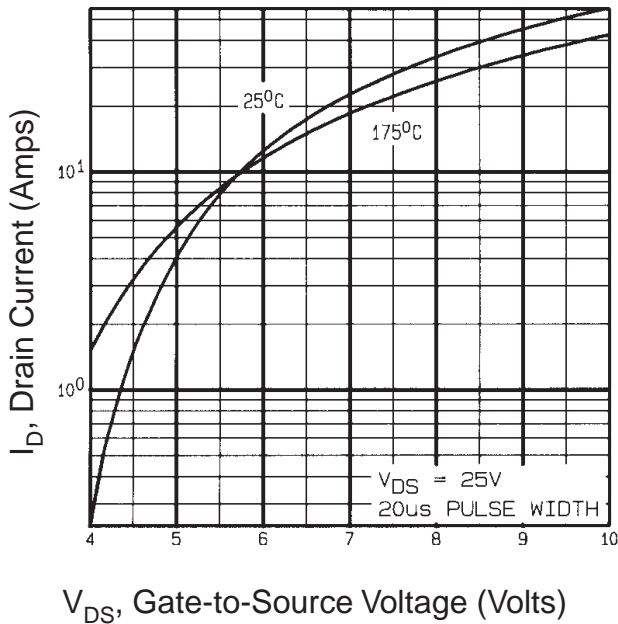


Fig. 3 Typical Transfer Characteristics

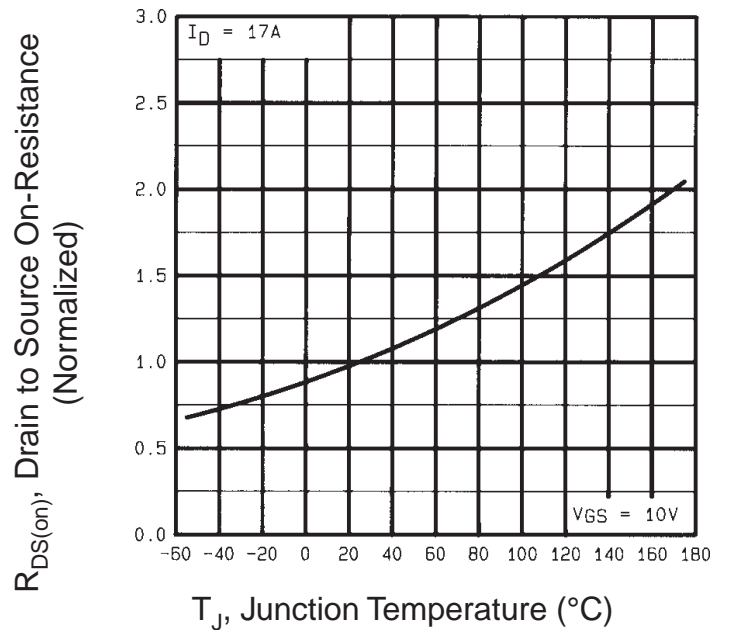


Fig. 4 Normalized On-Resistance vs. Temperature

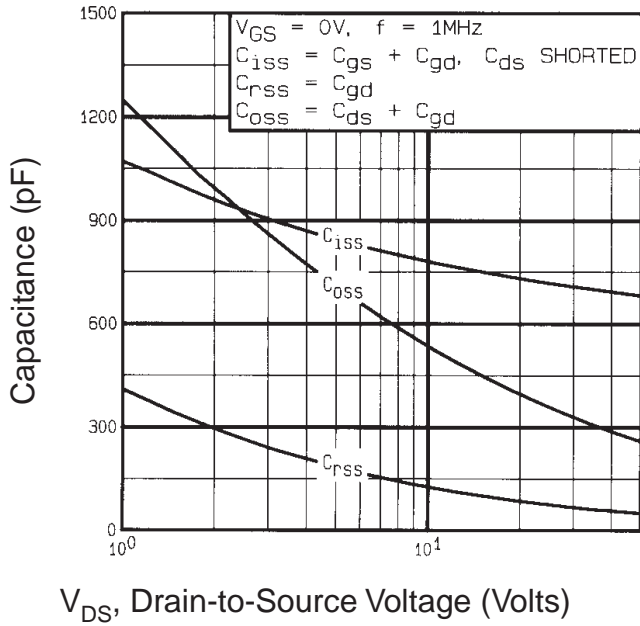


Fig. 5 Typical Capacitance vs. Drain-to-Source Voltage

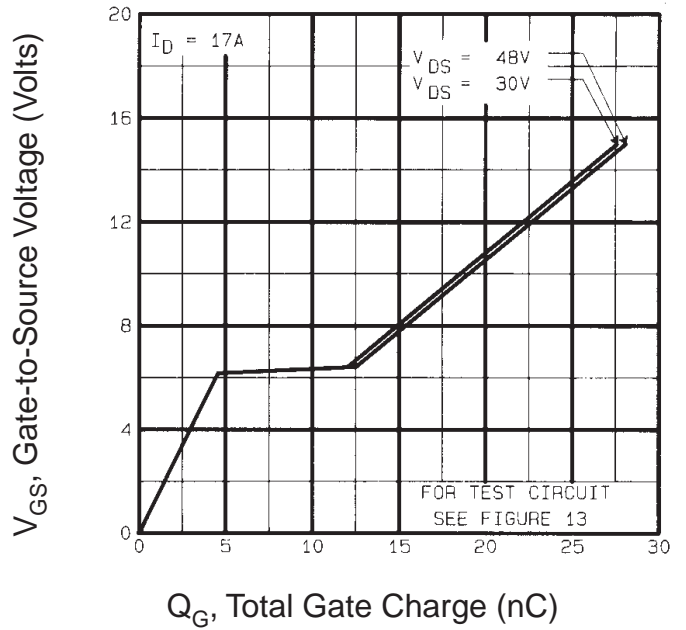


Fig. 6 Typical Gate Charge vs. Gate-to-Source Voltage

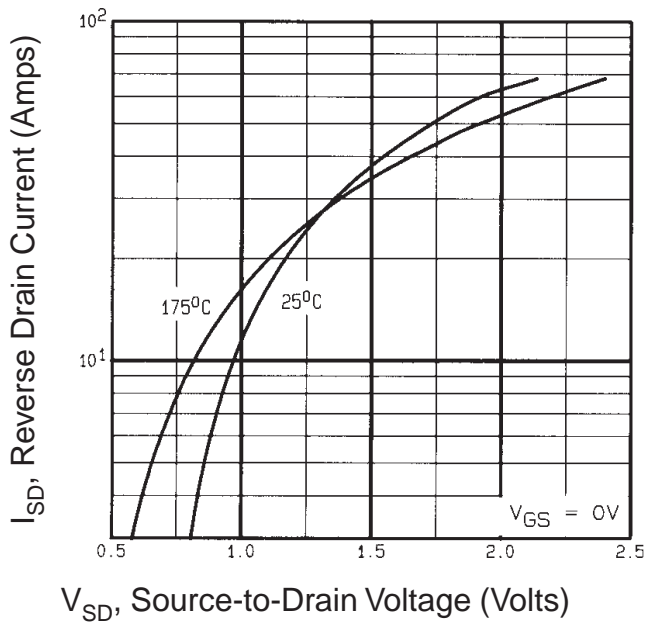


Fig. 7 Typical Source-Drain Diode Forward Voltage

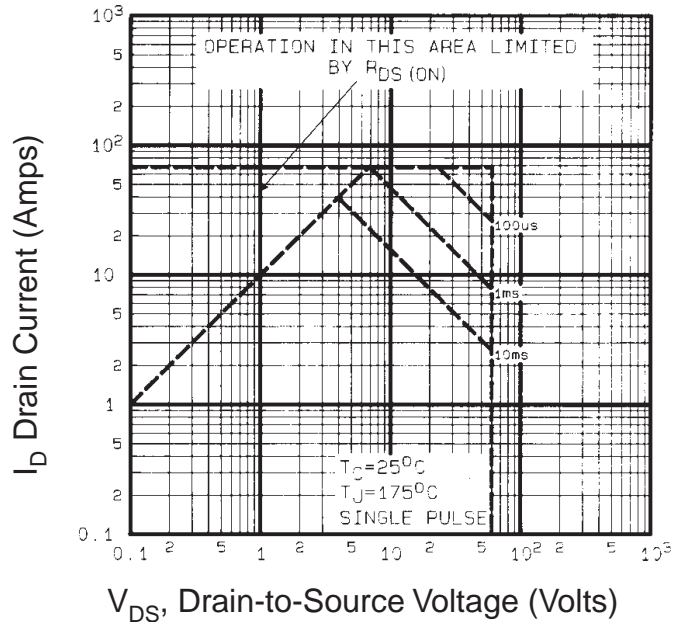


Fig. 8 Maximum Safe Operating Area

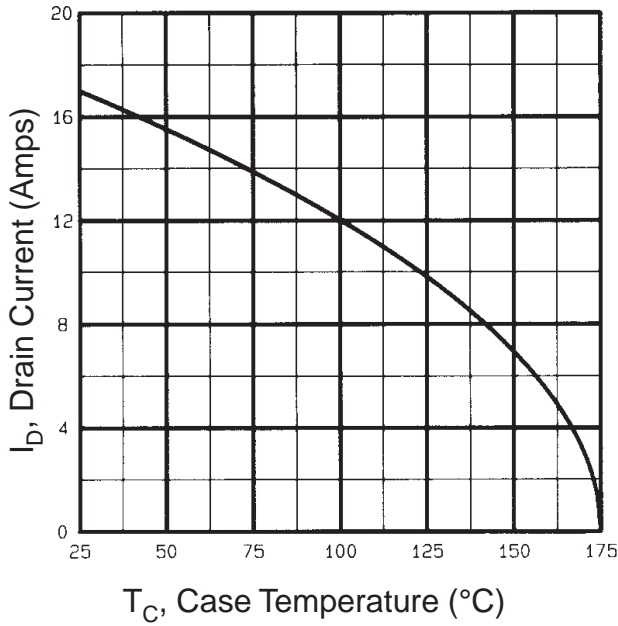


Fig. 9 Maximum Drain Current vs. Case Temperature

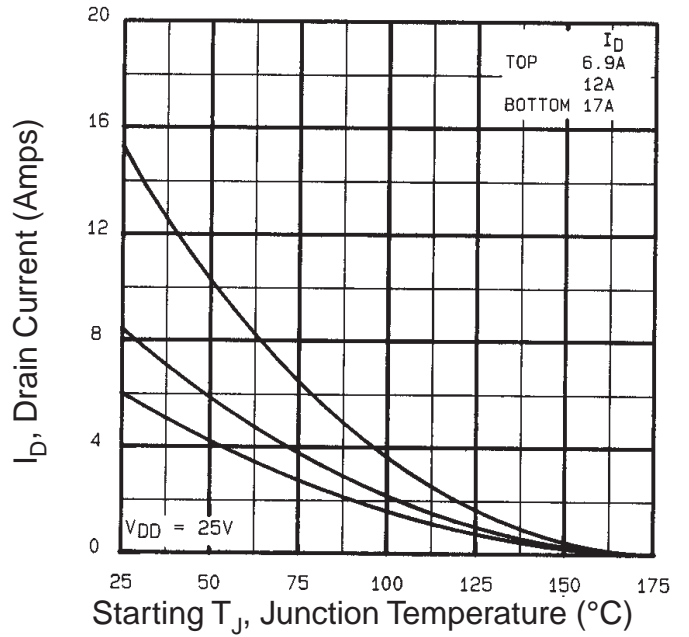


Fig. 12c Maximum Avalanche Energy vs. Drain Current

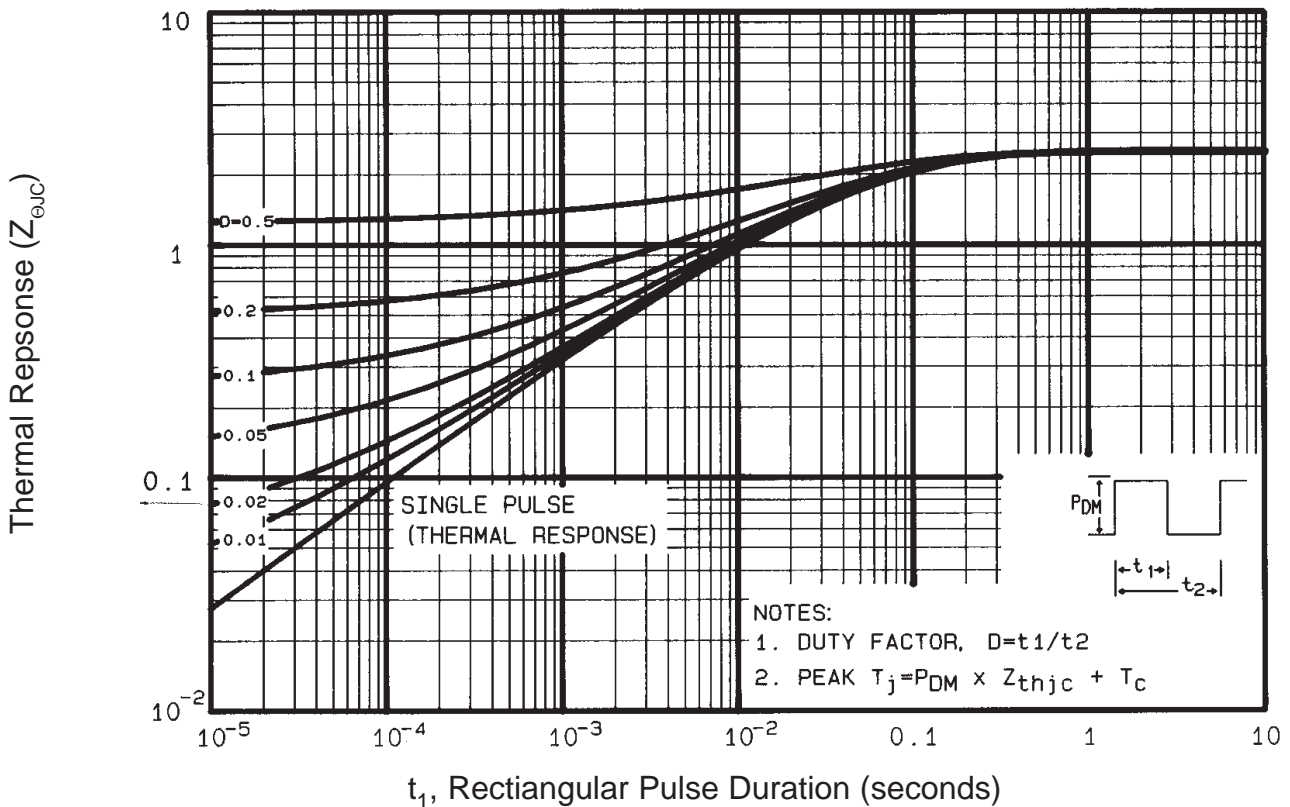


Fig. 11 Maximum Effective Transient Thermal Impedance, Junction-to-Case

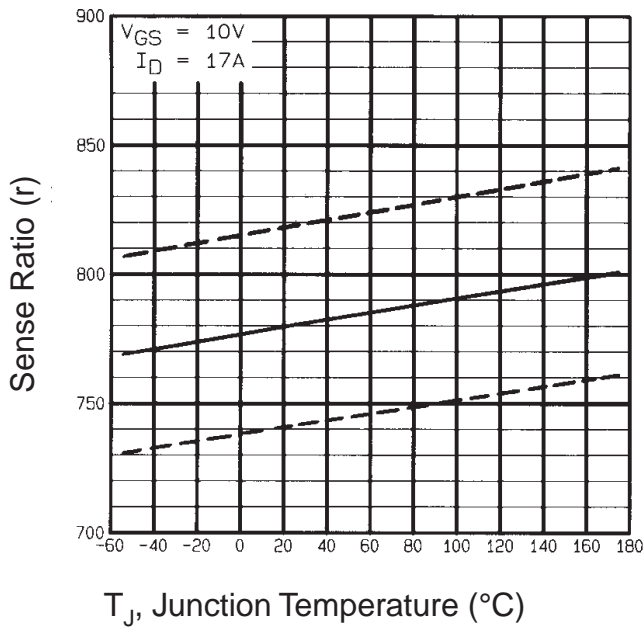


Fig. 15 Typical HEXSense Ratio vs. Junction Temperature

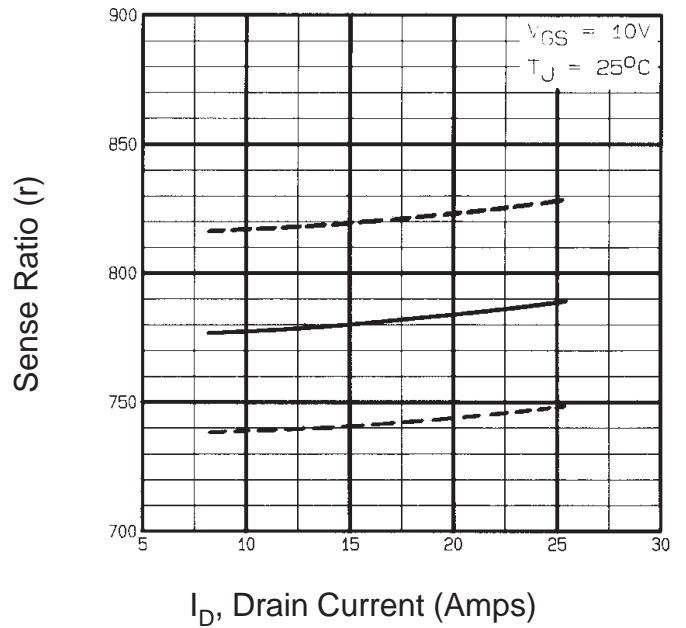


Fig. 16 Typical HEXSense Ratio vs. Drain Current

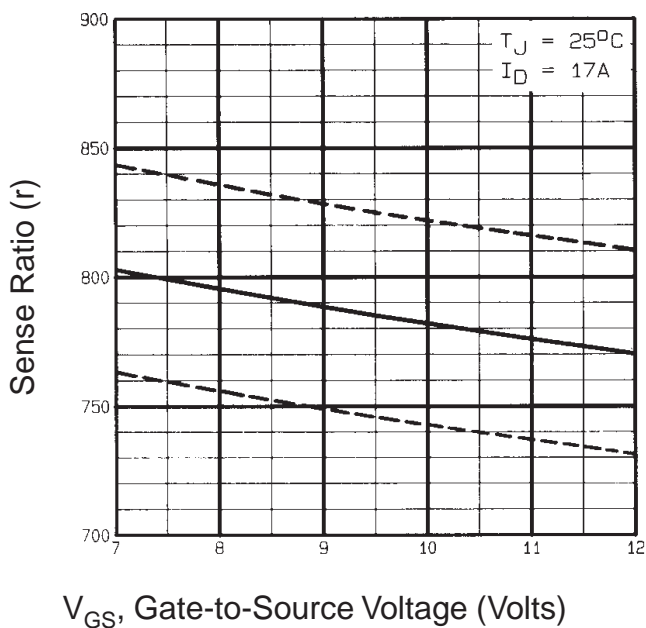


Fig. 17 Typical HEXSense Ratio vs. Gate Voltage

Mechanical drawings, Appendix A
Part marking information, Appendix B
Test Circuit diagrams, Appendix C

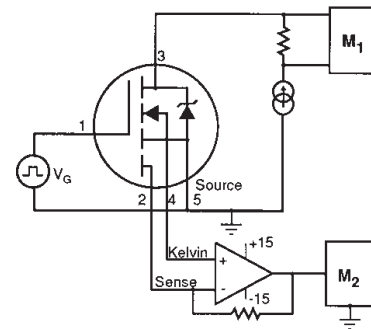


Fig. 18 HEXSense Ratio Test Circuit

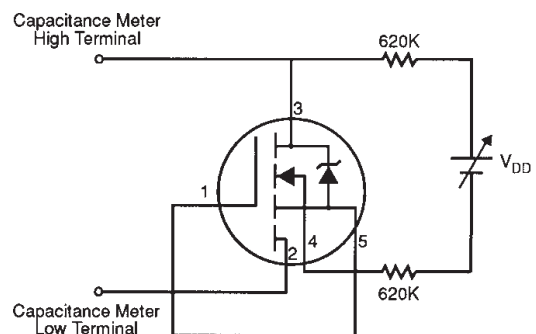


Fig. 19 HEXSense Sensing Cell Output Capacitance Test Circuit